

N-Channel Reduced Q_g , Fast Switching MOSFET

PRODUCT SUMMARY

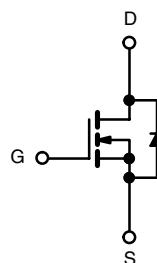
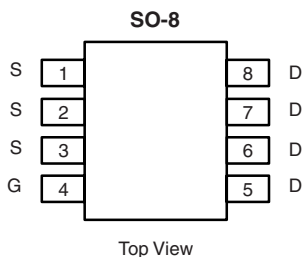
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
30	0.0185 at $V_{GS} = 10$ V	9
	0.030 at $V_{GS} = 4.5$ V	7

FEATURES

- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET® Power MOSFET
- High-Efficient PWM Optimized
- 100 % UIS and R_g Tested



RoHS
COMPLIANT
HALOGEN
FREE
Available



N-Channel MOSFET

Ordering Information: Si4800BDY-T1-E3 (Lead (Pb)-free)
Si4800BDY-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

Parameter	Symbol	10 s	Steady State	Unit
Drain-Source Voltage	V_{DS}	30		V
Gate-Source Voltage	V_{GS}	± 25		
Continuous Drain Current ($T_J = 150$ °C) ^{a, b}	$T_A = 25$ °C	I_D	9	6.5
	$T_A = 70$ °C		7.0	5.0
Pulsed Drain Current (10 μ s Pulse Width)	I_{DM}	40		A
Continuous Source Current (Diode Conduction) ^{a, b}	I_S	2.3		
Avalanche Current	I_{AS}	15		
Single-Pulse Avalanche Energy	E_{AS}	11.25		mJ
Maximum Power Dissipation ^{a, b}	$T_A = 25$ °C	P_D	2.5	1.3
	$T_A = 70$ °C		1.6	0.8
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Limits		Unit
		Typ.	Max.	
Maximum Junction-to-Ambient ^a	R_{thJA}	$t \leq 10$ s	40	50
		Steady State	70	95
Maximum Junction-to-Foot (Drain)	R_{thJF}	24	30	°C/W

Notes:

a. Surface Mounted on FR4 board.

b. $t \leq 10$ s.

MOSFET SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	0.8		1.8	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30\text{ V}$, $V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 30\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 55\text{ }^{\circ}\text{C}$			5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}$, $V_{GS} = 10\text{ V}$	30			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = 9\text{ A}$		0.0155	0.0185	Ω
		$V_{GS} = 4.5\text{ V}$, $I_D = 7\text{ A}$		0.023	0.030	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}$, $I_D = 9\text{ A}$		16		S
Diode Forward Voltage ^a	V_{SD}	$I_S = 2.3\text{ A}$, $V_{GS} = 0\text{ V}$		0.75	1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = 15\text{ V}$, $V_{GS} = 5.0\text{ V}$, $I_D = 9\text{ A}$		8.7	13	nC
Gate-Source Charge	Q_{gs}			1.5		
Gate-Drain Charge	Q_{gd}			3.5		
Gate Resistance	R_g		0.5	1.4	2.2	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}$, $R_L = 15\text{ }\Omega$ $I_D \cong 1\text{ A}$, $V_{GEN} = 10\text{ V}$, $R_g = 6\text{ }\Omega$		7	15	ns
Rise Time	t_r			12	20	
Turn-Off Delay Time	$t_{d(off)}$			32	50	
Fall Time	t_f			14	25	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 2.3\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$		30	60	

Notes:

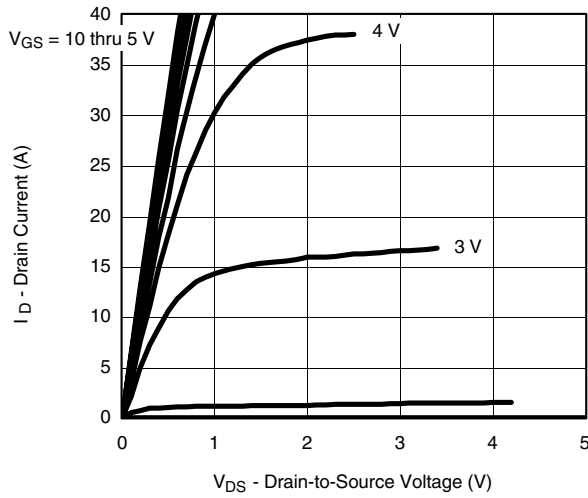
a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

b. Guaranteed by design, not subject to production testing.

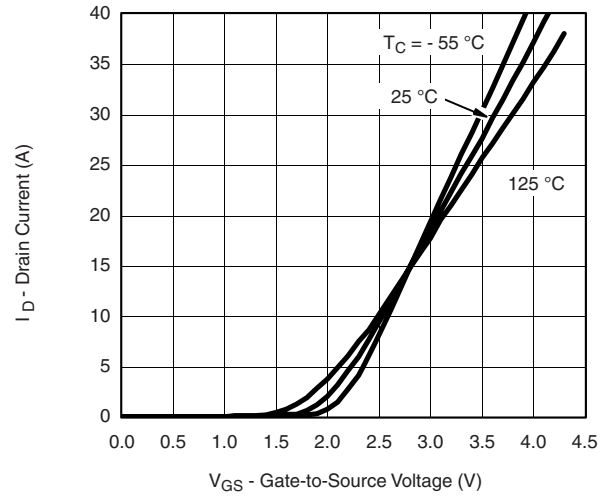
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



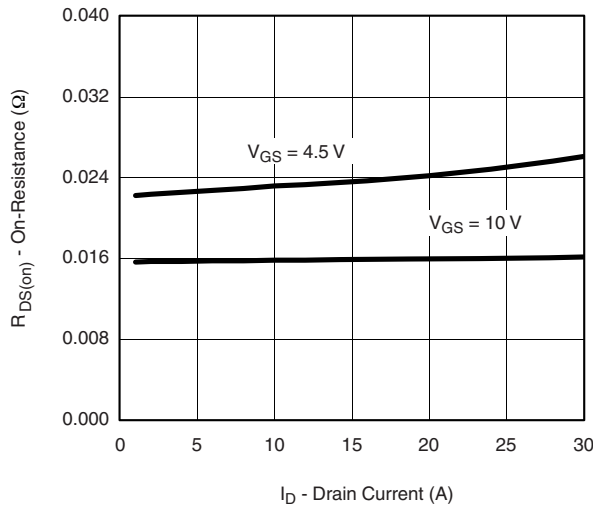
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



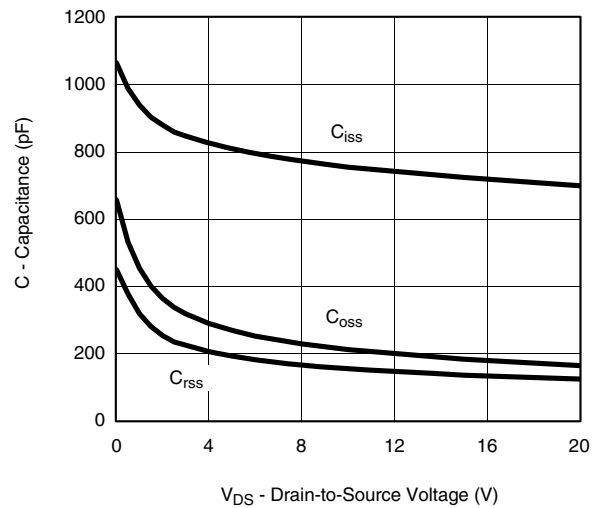
Output Characteristics



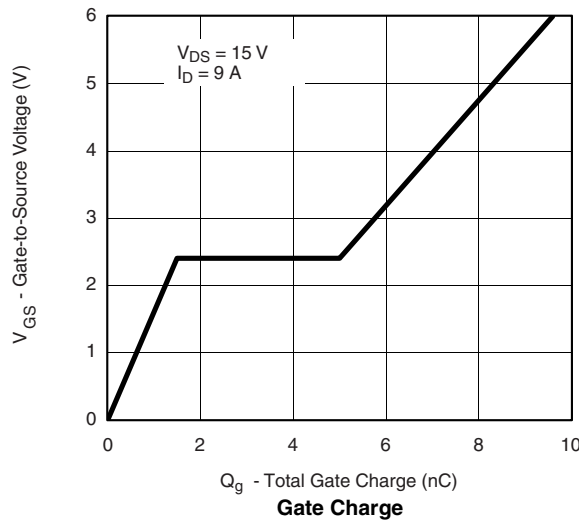
Transfer Characteristics



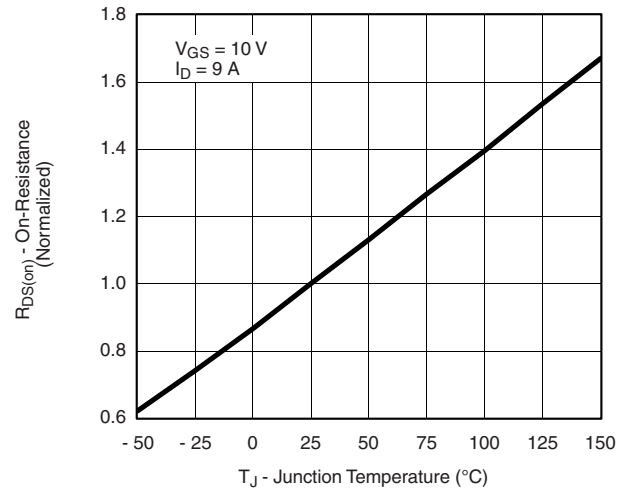
On-Resistance vs. Drain Current



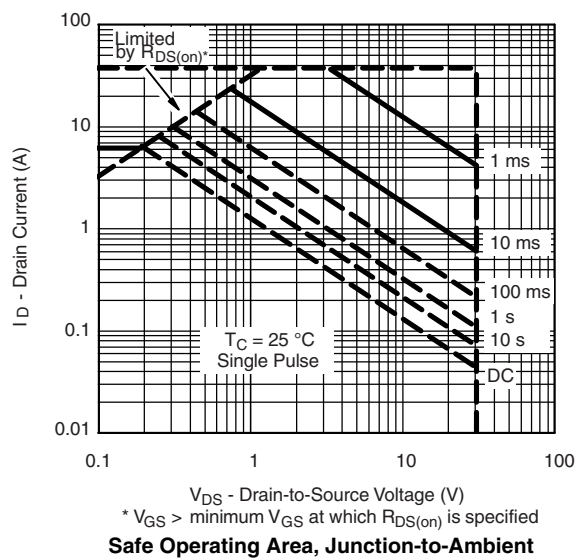
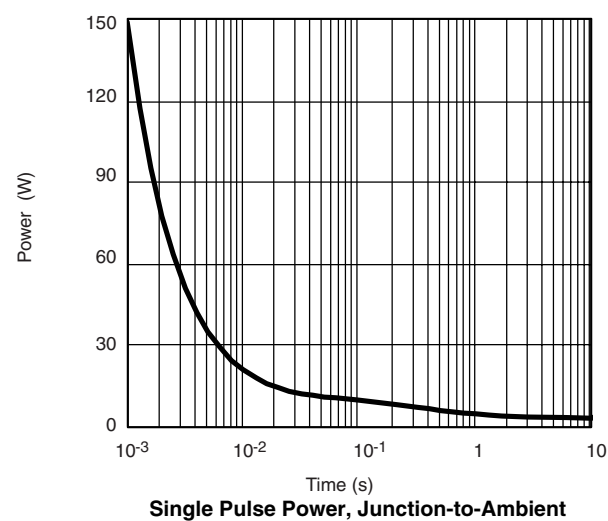
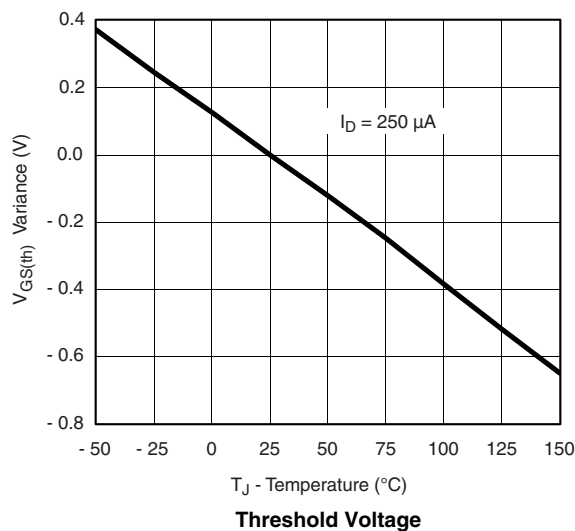
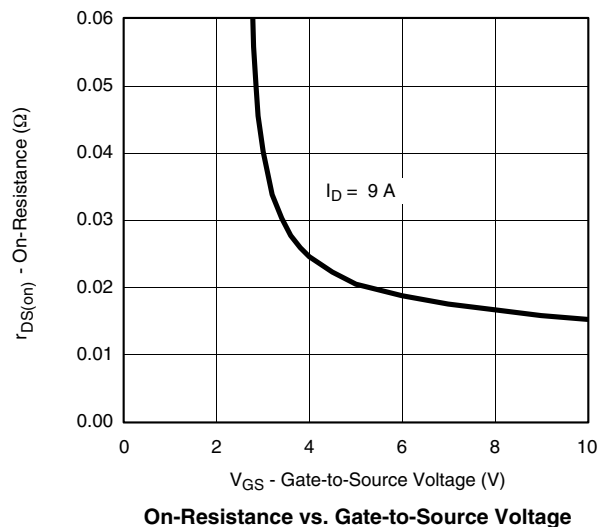
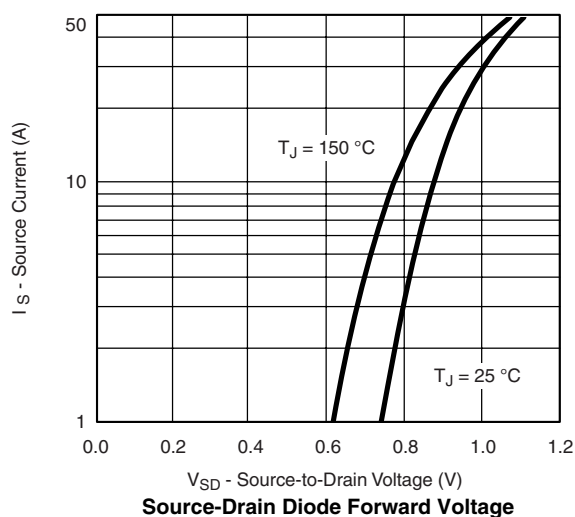
Capacitance



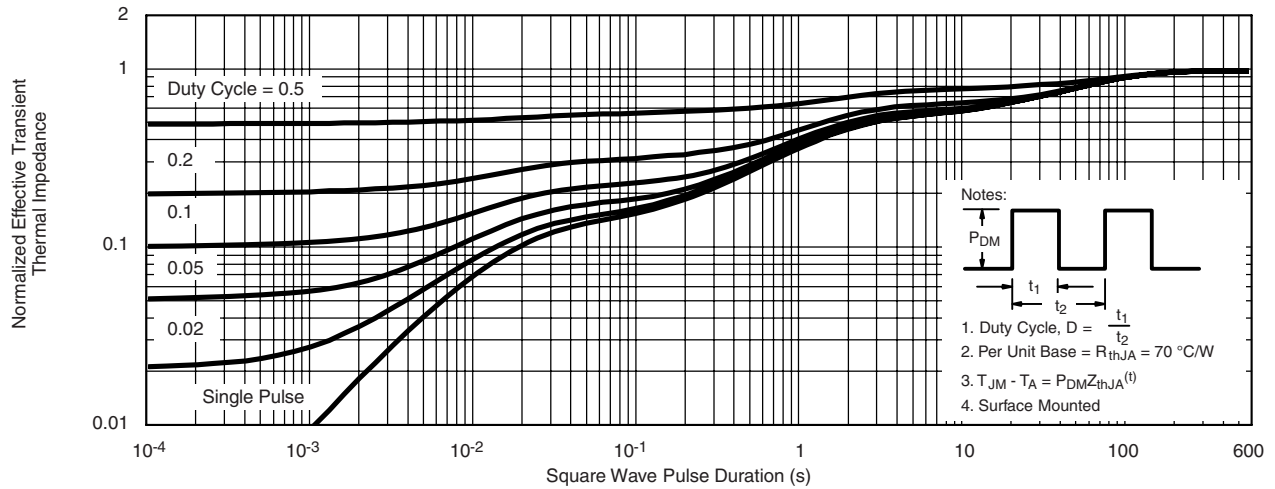
Gate Charge



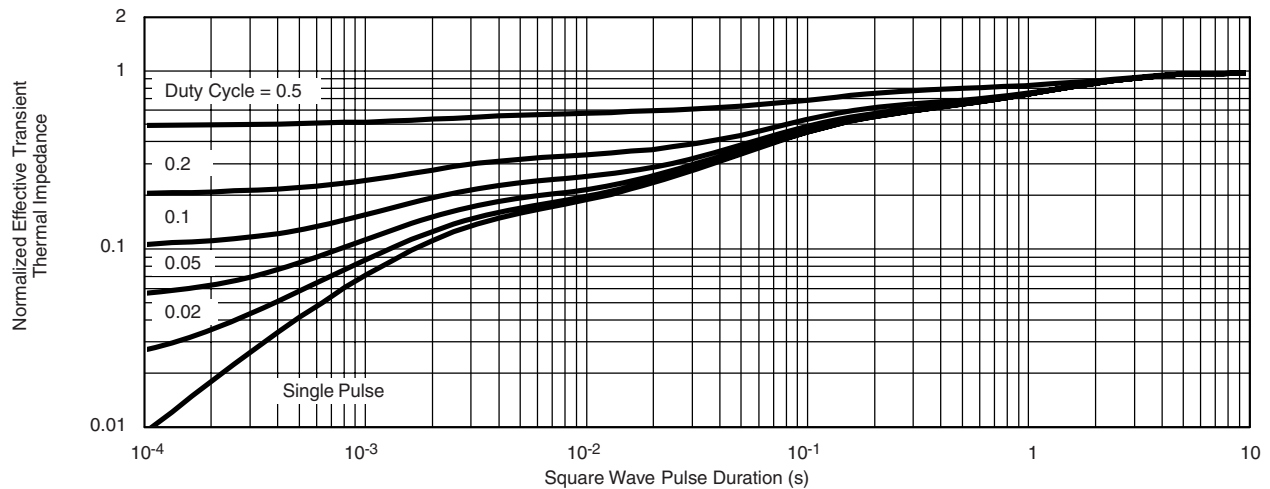
On-Resistance vs. Junction Temperature

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

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